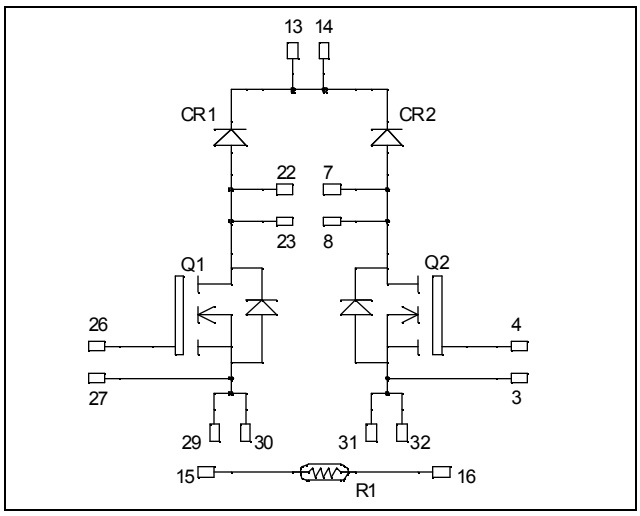
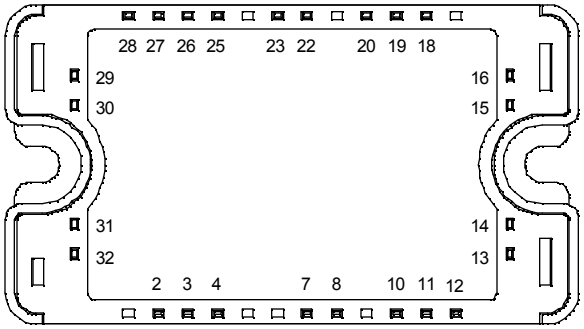
APTC80DDA15T3

Dual Boost chopper Super Junction MOSFET Power Module

V_{DSS} = 800V
R_{DSon} = 150mΩ max @ Tj = 25°C
I_D = 28A @ Tc = 25°C





All multiple inputs and outputs must be shorted together
Example: 13/14 ; 29/30 ; 22/23 …

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- COOLMOS Power Semiconductors
  - Ultra low R_{DSon}
  - Low Miller capacitance
  - Ultra low gate charge
  - Avalanche energy rated
  - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
  - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a single boost of twice the current capability

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{DSS}	Drain - Source Breakdown Voltage		800	V
I_D	Continuous Drain Current	T_c = 25°C	28	A
		T_c = 80°C	21	
I_{DM}	Pulsed Drain current		110	
V_{GS}	Gate - Source Voltage		±30	V
R_{DSon}	Drain - Source ON Resistance		150	mΩ
P_D	Maximum Power Dissipation	T_c = 25°C	277	W
I_{AR}	Avalanche current (repetitive and non repetitive)		24	A
E_{AR}	Repetitive Avalanche Energy		0.5	mJ
E_{AS}	Single Pulse Avalanche Energy		670	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handing Procedures Should Be Followed.

All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
BV_{DSS}	Drain - Source Breakdown Voltage	V_{GS} = 0V, I_D = 375µA		800			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS} = 0V, V_{DS} = 800V	T_j = 25°C			50	µA
		V_{GS} = 0V, V_{DS} = 800V	T_j = 125°C			375	
$R_{DS(on)}$	Drain – Source on Resistance	V_{GS} = 10V, I_D = 14A				150	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 2mA		2.1	3	3.9	V
I_{GSS}	Gate – Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0V				±150	nA

Dynamic Characteristics

Symbol	*Characteristic*	*Test Conditions*	*Min*	*Typ*	*Max*	*Unit*
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} = 25V f = 1MHz		4507		pF
C_{oss}	Output Capacitance			2092		
C_{rss}	Reverse Transfer Capacitance			108		
Q_g	Total gate Charge	V_{GS} = 10V V_{Bus} = 400V I_D = 28A		180		nC
Q_{gs}	Gate – Source Charge			22		
Q_{gd}	Gate – Drain Charge			90		
$T_{d(on)}$	Turn-on Delay Time	**Inductive switching @125°C** V_{GS} = 15V V_{Bus} = 533V I_D = 28A R_G = 2.5Ω		10		ns
T_r	Rise Time			13		
$T_{d(off)}$	Turn-off Delay Time			83		
T_f	Fall Time			35		
E_{on}	Turn-on Switching Energy ❶	**Inductive switching @ 25°C** V_{GS} = 15V, V_{Bus} = 533V I_D = 28A, R_G = 2.5Ω		486		µJ
E_{off}	Turn-off Switching Energy ❷			278		
E_{on}	Turn-on Switching Energy ❶	**Inductive switching @ 125°C** V_{GS} = 15V, V_{Bus} = 533V I_D = 28A, R_G = 2.5Ω		850		µJ
E_{off}	Turn-off Switching Energy ❷			342		

Diode ratings and characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1000			V
I_{RM}	Maximum Reverse Leakage Current	V_R=1000V	T_j = 25°C			250	µA
			T_j = 125°C			500	
$I_{F(AV)}$	Maximum Average Forward Current	50% duty cycle	T_c = 100°C		60		A
V_F	Diode Forward Voltage	I_F = 60A			1.9	2.5	V
		I_F = 120A			2.2		
		I_F = 60A	T_j = 125°C		1.7		
t_{rr}	Reverse Recovery Time	I_F = 60A V_R = 667V di/dt=200A/µs	T_j = 25°C		280		ns
			T_j = 125°C		350		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		760		nC
			T_j = 125°C		3600		

❶ E_{on} includes diode reverse recovery.
❷ In accordance with JEDEC standard JESD24-1.

Thermal and package characteristics

Symbol	Characteristic			Min	Typ	Max	Unit
R_{thJC}	Junction to Case		IGBT			0.45	°C/W
			Diode			0.9	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			2500			V
T_J	Operating junction temperature range			-40		150	°C
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4			4.7	N.m
Wt	Package Weight					110	g

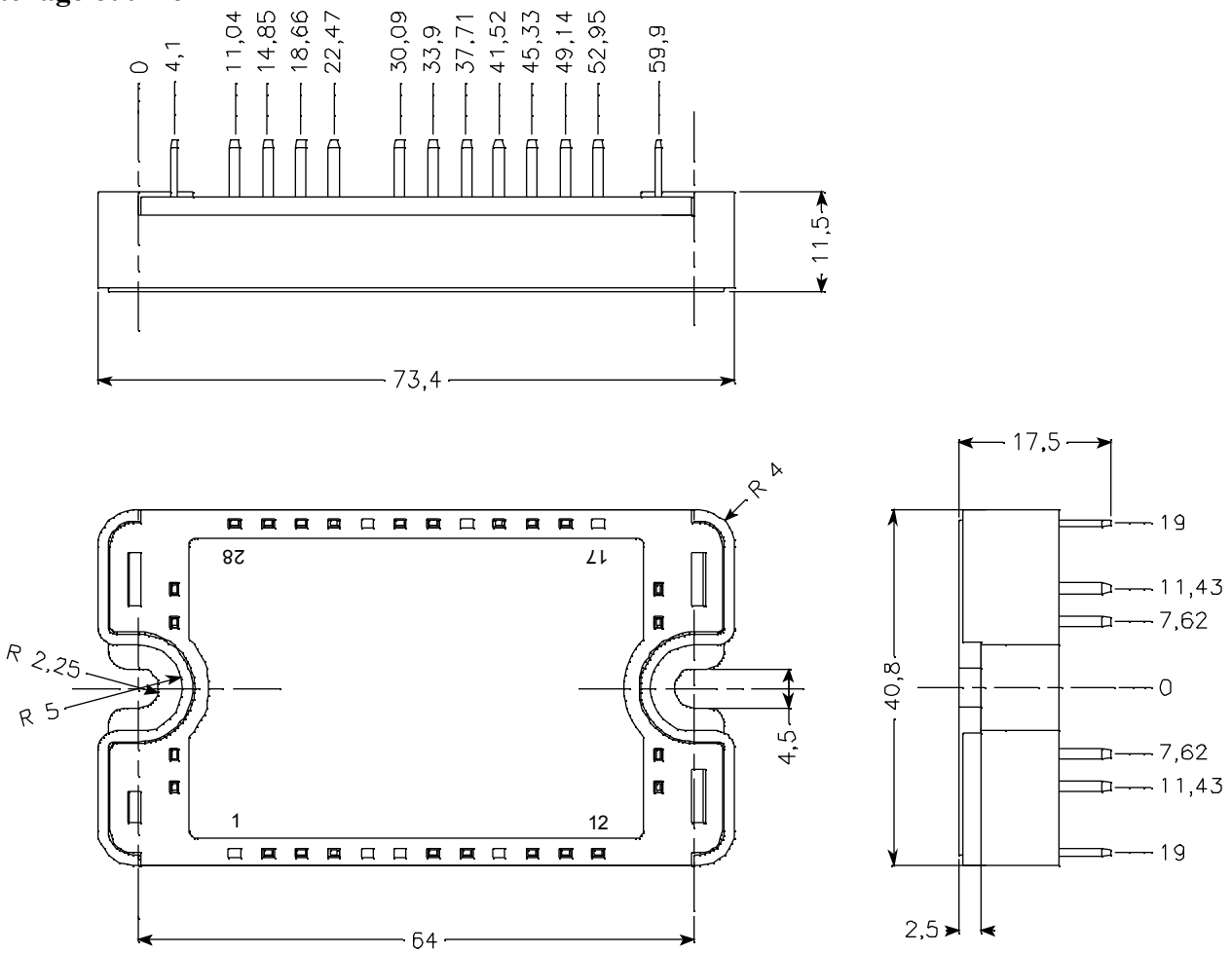
Temperature sensor NTC

Symbol	Characteristic	Min	Typ	Max	Unit
R_{25}	Resistance @ 25°C		68		kΩ
$B_{25/85}$	T_{25} = 298.16 K		4080		K

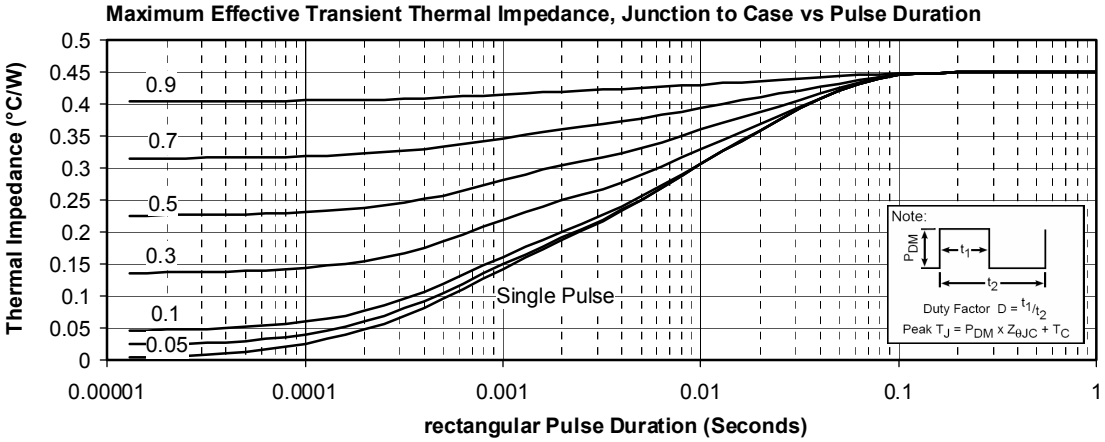
$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

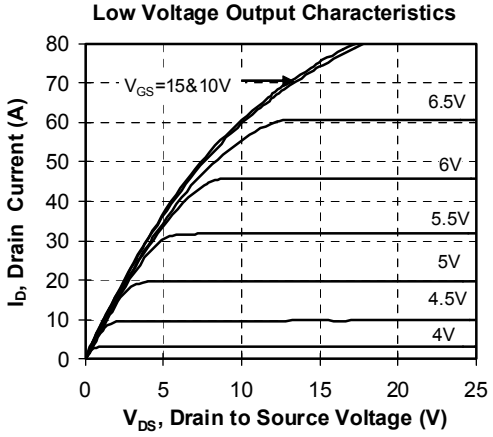
T: Thermistor temperature
R_T: Thermistor value at T

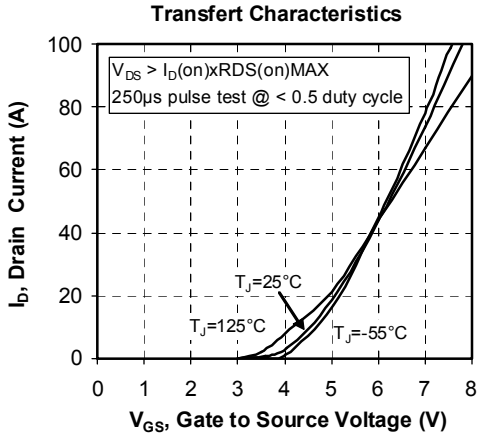
Package outline

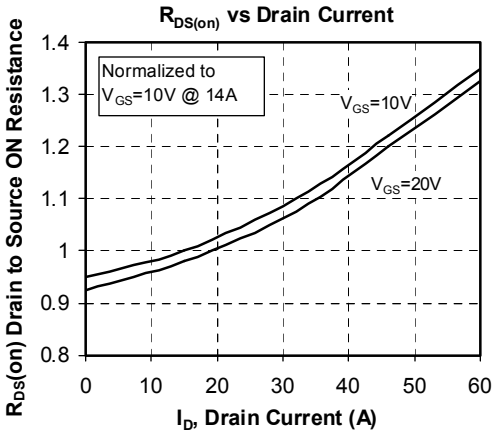


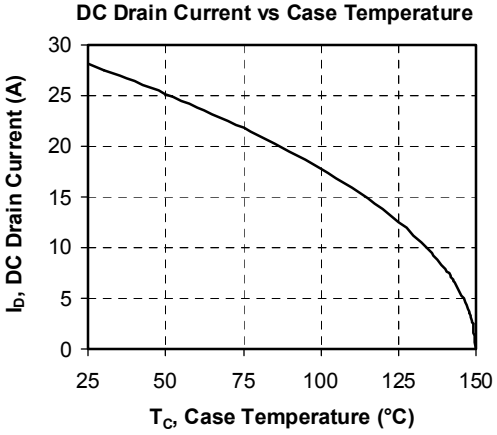
Typical Performance Curve



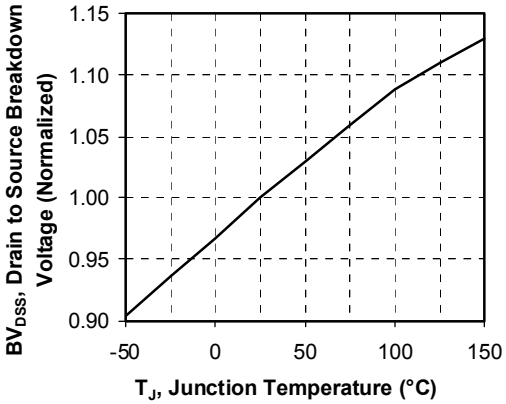




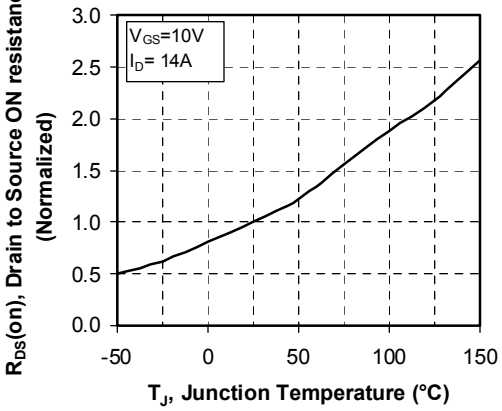




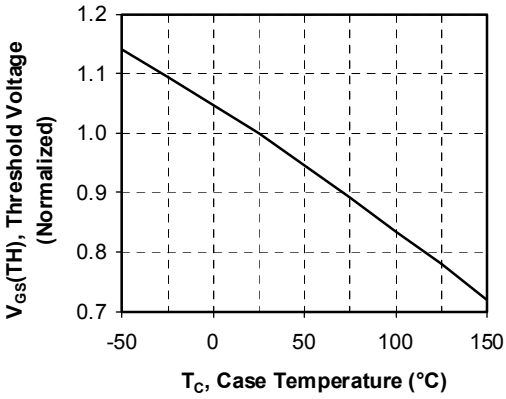
Breakdown Voltage vs Temperature



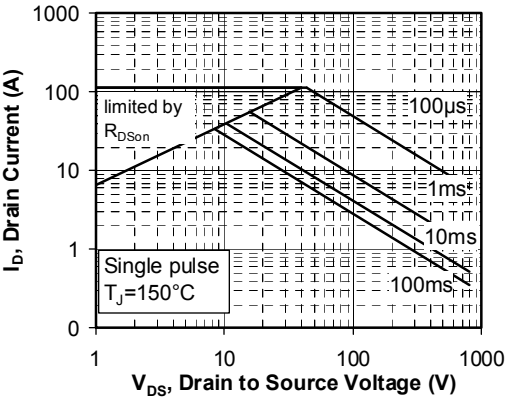
ON resistance vs Temperature



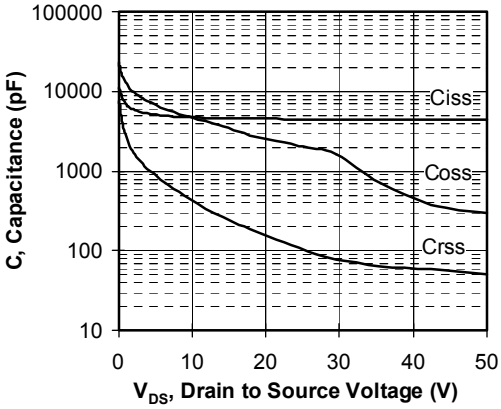
Threshold Voltage vs Temperature



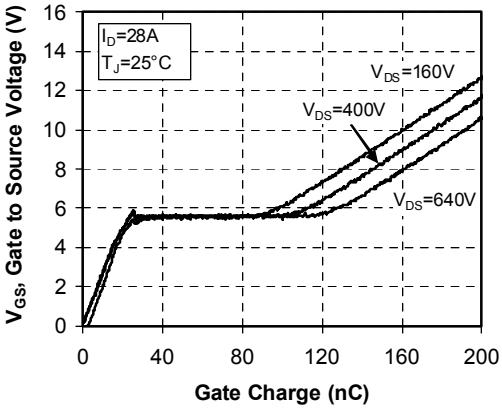
Maximum Safe Operating Area



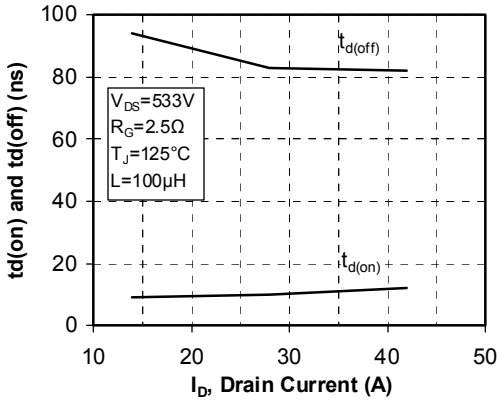
Capacitance vs Drain to Source Voltage



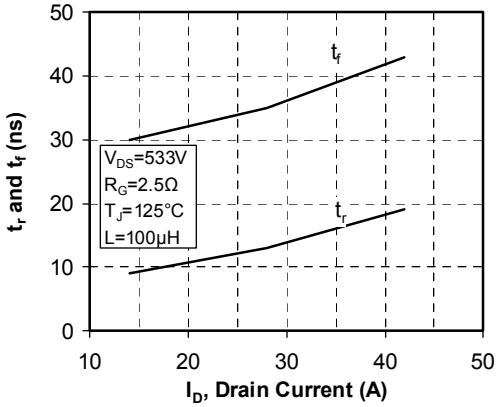
Gate Charge vs Gate to Source Voltage



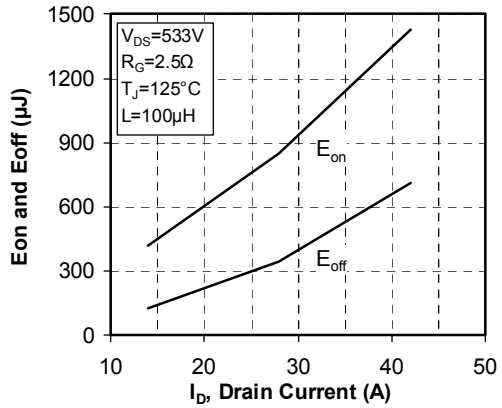
Delay Times vs Current



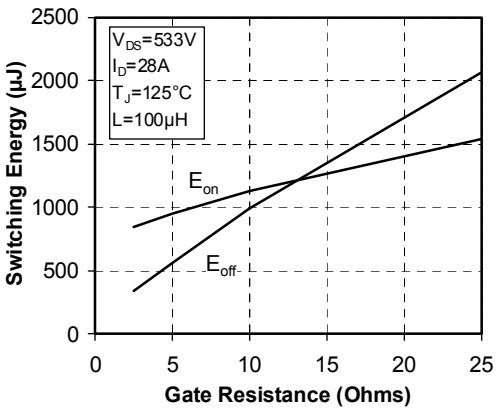
Rise and Fall times vs Current



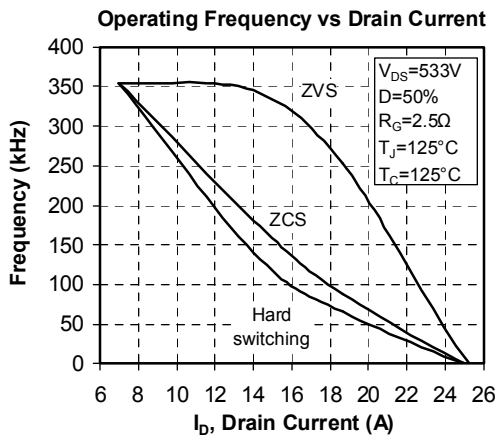
Switching Energy vs Current



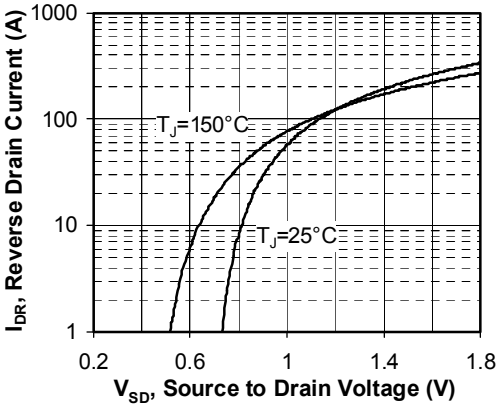
Switching Energy vs Gate Resistance



Operating Frequency vs Drain Current



Source to Drain Diode Forward Voltage



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